VS-80EBU02



Vishay Semiconductors

Ultrafast Soft Recovery Diode, 80 A FRED Pt[®]



PowerTab[®]

PRODUCT SUMMARY				
Package	PowerTab [®]			
I _{F(AV)}	80 A			
V _R	200 V			
V _F at I _F	0.79 V			
t _{rr} (typ.)	See recovery table			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- · Screw mounting only
- Designed and qualified according to JEDEC[®]-JESD 47
- PowerTab[®] package
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		200	V	
Continuous forward current	I _{F(AV)}	T _C = 112 °C	80		
Single pulse forward current	I _{FSM}	T _C = 25 °C	800	А	
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	160		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _r	I _R = 50 μA	200	-	-	
Forward voltage V _F	I _F = 80 A	-	0.98	1.13	V	
	۷F	I _F = 80 A, T _J = 175 °C	-	0.79	0.92	
Reverse leakage current	1	$V_R = V_R$ rated	-	-	50	μA
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	2	mA
Junction capacitance	CT	V _R = 200 V -		89	-	pF
Series inductance	Ls	Measured lead to lead 5 mm from package body - 3.5 -		nH		





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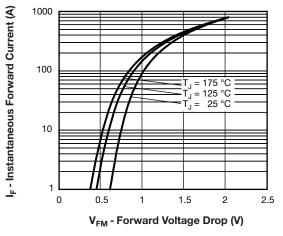


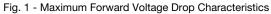
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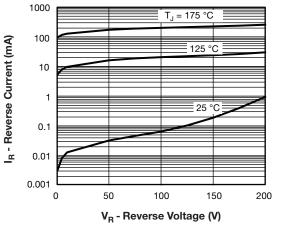
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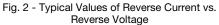
DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS	
		I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	-	35	
Reverse recovery time t _{rr}	T _J = 25 °C		-	32	-	ns	
		T _J = 125 °C		-	52	-	
Peak recovery current	I _{RRM}	T _J = 25 °C	I _F = 80 A V _R = 160 V dI _F /dt = 200 A/μs	-	4.4	-	A
		T _J = 125 °C		-	8.8	-	
Reverse recovery charge Q _{rr}	$Q_{rr} \qquad \frac{T_J = 25 \text{ °C}}{T_J = 125 \text{ °C}}$	T _J = 25 °C		-	70	-	
			-	240	-	no	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance, junction to case	R _{thJC}		-	-	0.70	°C/W	
Thermal resistance, junction to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	0/11	
Weight			-	-	5.02	g	
weight			-	0.18	-	oz.	
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)	
Marking device		Case style PowerTab®		80EE	3U02		





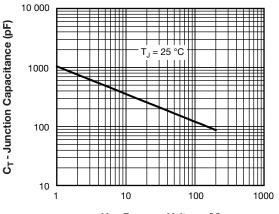




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V_R - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

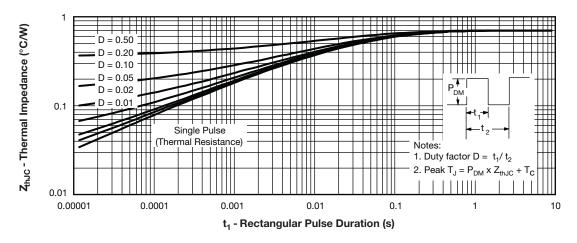
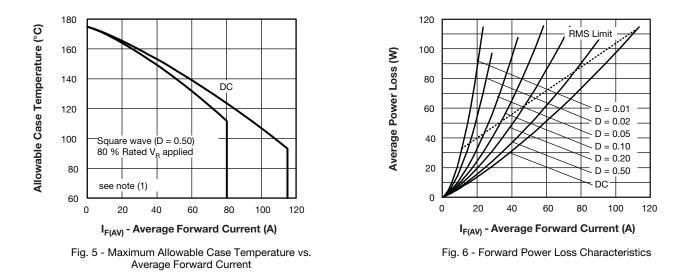


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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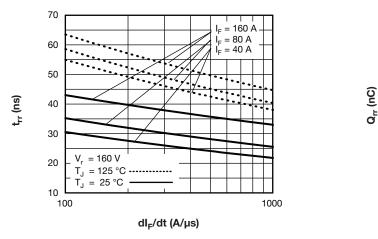
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

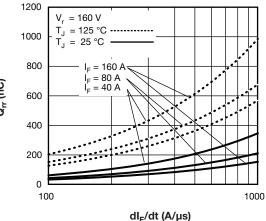


Fig. 8 - Typical Stored Charge vs. dl_F/dt

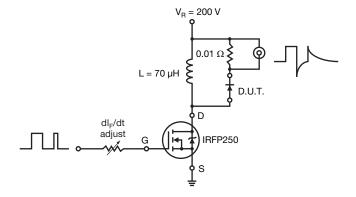


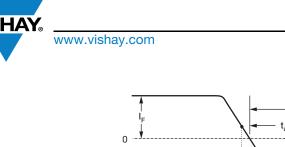
Fig. 9 - Reverse Recovery Parameter Test Circuit

Note

SHA



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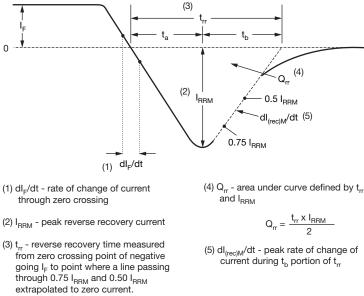


Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	80	E	В	U	02
	1	2	3	4	5	6
	1 .		5	niconduc		oduct
	2 -	Cur	rent rati	ng (80 =	: 80 A)	
	3 -	Sing	gle diod	е		
	4 -	- Pov	verTab®	(ultrafa	st/hyper	fast only)
	5 -	Ultr	afast ree	covery		
	6 -	· Volt	tage rati	ng (02 =	= 200 V)	

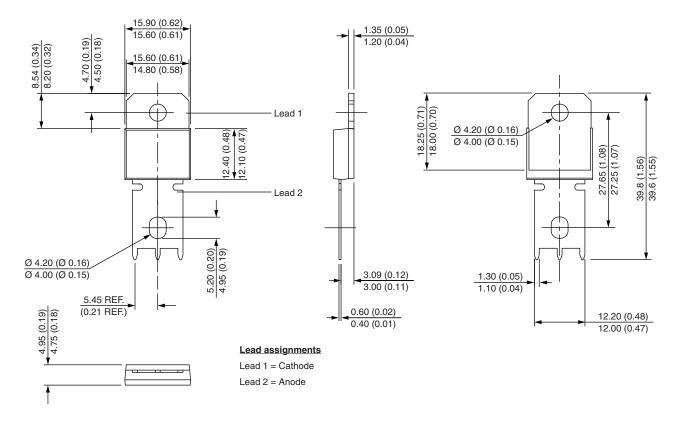
LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95240				
Part marking information	www.vishay.com/doc?95370			
Application note	www.vishay.com/doc?95179			



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DIMENSIONS in millimeters (inches)





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